

**RADIATION HARDENED  
POWER MOSFET  
SURFACE MOUNT (SMD-1)**

**IRHN9150  
JANSR2N7422U  
100V, P-CHANNEL**

REF: MIL-PRF-19500/662

**RAD Hard™ HEXFET® TECHNOLOGY**

**Product Summary**

Part Number	Radiation Level	RDS(on)	Id	QPL Part Number
IRHN9150	100K Rads (Si)	0.080Ω	-22A	JANSR2N7422U
IRHN93150	300K Rads (Si)	0.080Ω	-22A	JANSF2N7422U



International Rectifier's RADHard HEXFET™ technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rds on and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
Id @ VGS = -12V, TC = 25°C	Continuous Drain Current	-22	A
Id @ VGS = -12V, TC = 100°C	Continuous Drain Current	-14	
IdM	Pulsed Drain Current ①	-88	
PD @ TC = 25°C	Max. Power Dissipation	150	W
	Linear Derating Factor	1.2	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
IAR	Avalanche Current ①	-22	A
EAR	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-23	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	PCKG Mounting Surface Temp.	300 (for 5s)	
	Weight	2.6 (typical)	g

For footnotes refer to the last page

**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	-100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	-0.093	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	0.080	Ω	V <sub>GS</sub> = -12V, I <sub>D</sub> = -14A ④
		—	—	0.085		V <sub>GS</sub> = -12V, I <sub>D</sub> = -22A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	-2.0	—	-4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1.0mA
g <sub>fs</sub>	Forward Transconductance	11	—	—	S	V <sub>DS</sub> = -15V, I <sub>DS</sub> = -14A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	-25	μA	V <sub>DS</sub> = -80V, V <sub>GS</sub> = 0V
		—	—	-250		V <sub>DS</sub> = -80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	-100	nA	V <sub>GS</sub> = -20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	—	200	nC	V <sub>GS</sub> = -12V, I <sub>D</sub> = -22A V <sub>DS</sub> = -50V
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	35		
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	48		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	40	ns	V <sub>DD</sub> = -50V, I <sub>D</sub> = -22A, V <sub>GS</sub> = -12V, R <sub>G</sub> = 2.35Ω
t <sub>r</sub>	Rise Time	—	—	170		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	190		
t <sub>f</sub>	Fall Time	—	—	190		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C <sub>iss</sub>	Input Capacitance	—	4300	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1100	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	310	—		

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-22	A	
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	-88		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-3.0	V	T <sub>j</sub> = 25°C, I <sub>S</sub> = -22A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	300	ns	T <sub>j</sub> = 25°C, I <sub>F</sub> = -22A, di/dt ≤ -100A/μs
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	1.5	μC	V <sub>DD</sub> ≤ -50V ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	0.83	°C/W	soldered to a 1"sq. copper-clad board
R <sub>thJ-PCB</sub>	Junction-to-PC board	—	6.6	—		

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

## Radiation Characteristics

## IRHN9150, JANSR2N7422U

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation** <sup>⑤⑥</sup>

	Parameter	100K Rads(Si) <sup>1</sup>		300K Rads (Si) <sup>2</sup>		Units	Test Conditions
		Min	Max	Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	-100	—	-100	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V <sub>GS</sub> = -20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	100	—	100		V <sub>GS</sub> = 20 V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	-25	—	-25	μA	V <sub>DS</sub> = -80V, V <sub>GS</sub> = 0V
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (TO-3)	—	0.081	—	0.081	Ω	V <sub>GS</sub> = -12V, I <sub>D</sub> = -14A
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (SMD-1)	—	0.080	—	0.080	Ω	V <sub>GS</sub> = -12V, I <sub>D</sub> = -14A
V <sub>SD</sub>	Diode Forward Voltage <sup>④</sup>	—	-3.0	—	-3.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -22A

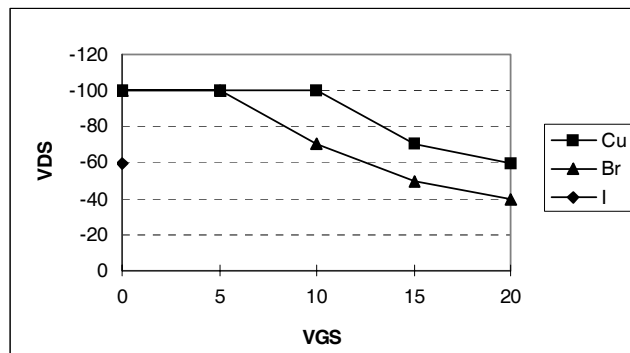
1. Part number IRHN9150 (JANSR2N7422U)

2. Part number IRHN93150 (JANSF2N7422U)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Typical Single Event Effect Safe Operating Area**

Ion	LET MeV/(mg/cm <sup>2</sup> )	Energy (MeV)	Range (μm)	V <sub>DS</sub> (V)				
				@V <sub>GS</sub> =0V	@V <sub>GS</sub> =5V	@V <sub>GS</sub> =10V	@V <sub>GS</sub> =15V	@V <sub>GS</sub> =20V
Cu	28	285	43	-100	-100	-100	-70	-60
Br	36.8	305	39	-100	-100	-70	-50	-40
I	59.9	345	32.8	-60	—	—	—	—



**Fig a. Typical Single Event Effect, Safe Operating Area**

For footnotes refer to the last page

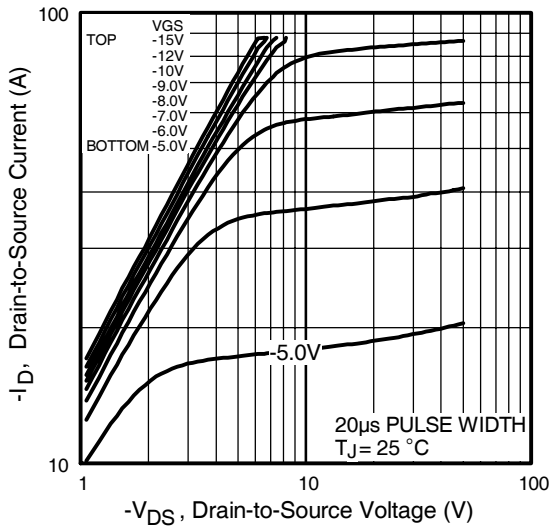


Fig 1. Typical Output Characteristics

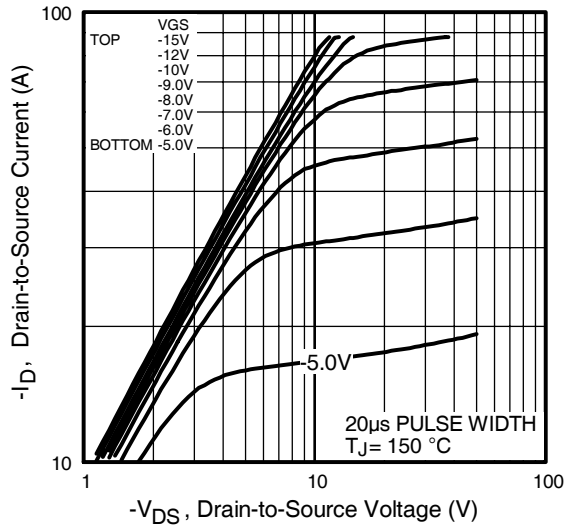


Fig 2. Typical Output Characteristics

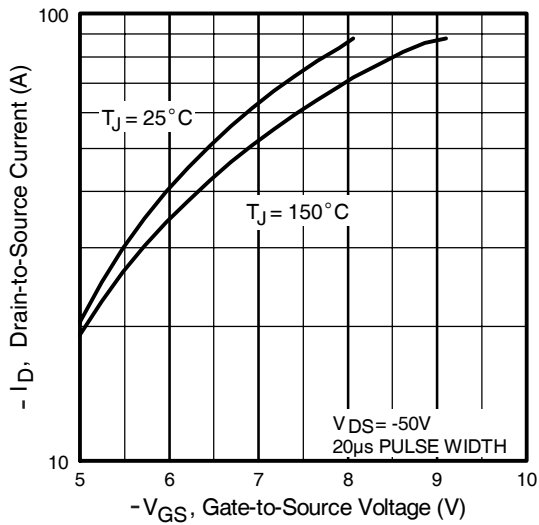


Fig 3. Typical Transfer Characteristics

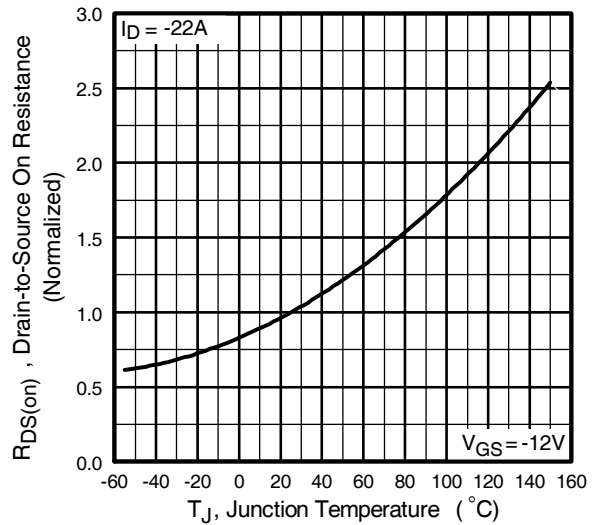


Fig 4. Normalized On-Resistance Vs. Temperature

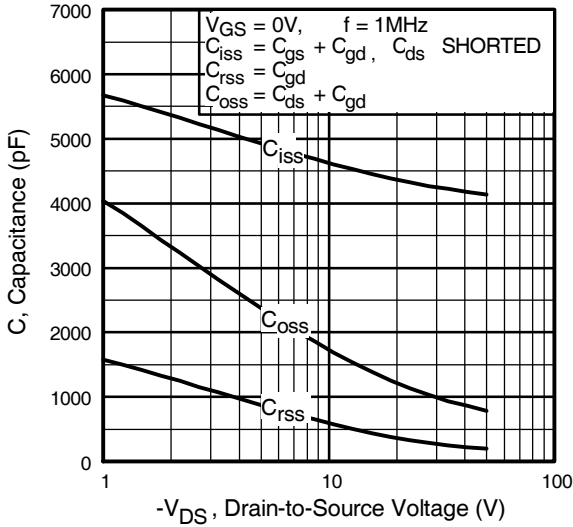


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

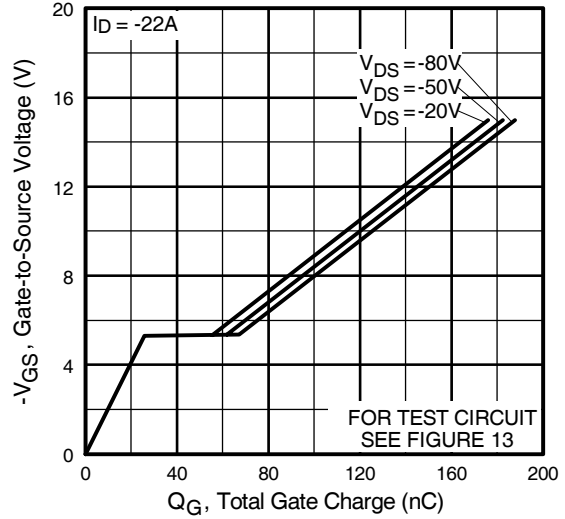


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

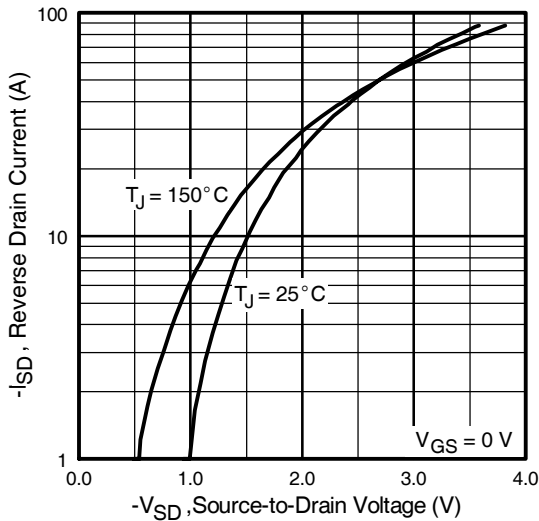


Fig7. Typical Source-Drain Diode Forward Voltage

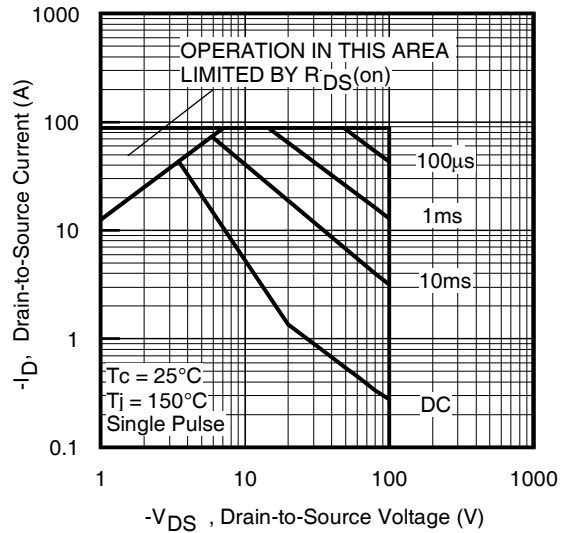
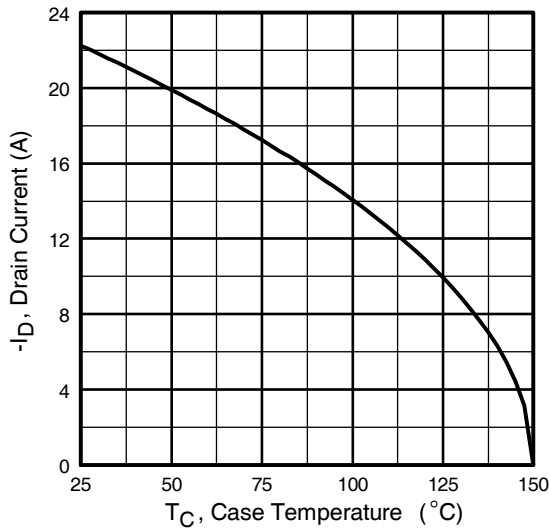
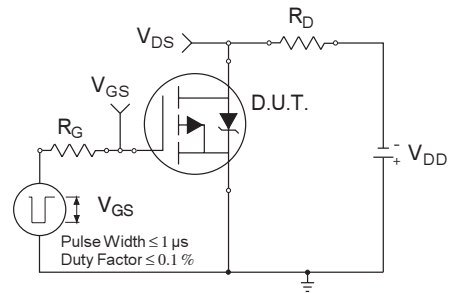


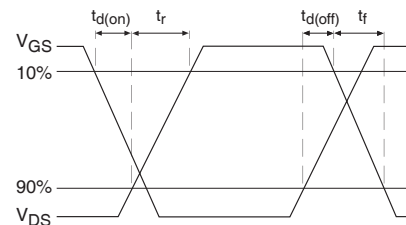
Fig8. Maximum Safe Operating Area



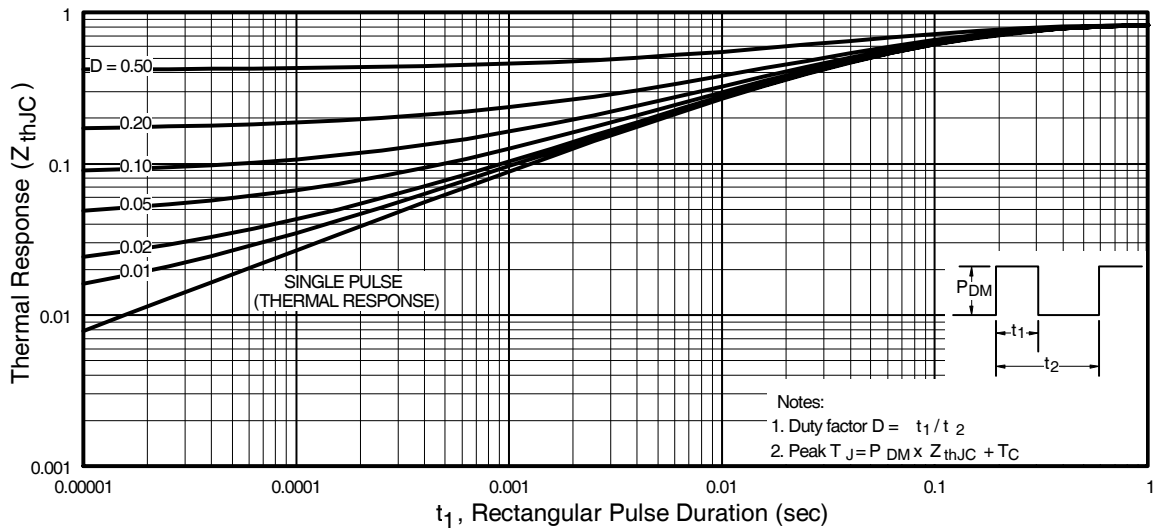
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

IRHN9150, JANSR2N7422U

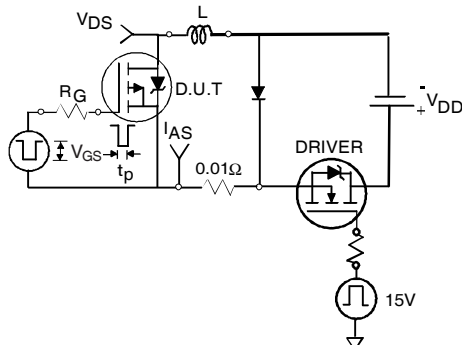


Fig 12a. Unclamped Inductive Test Circuit

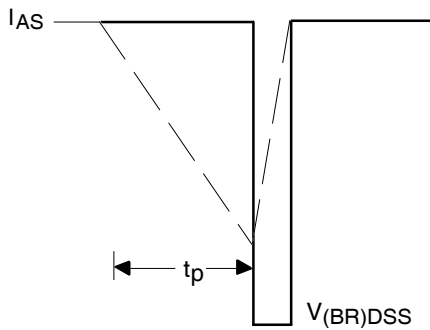


Fig 12b. Unclamped Inductive Waveforms

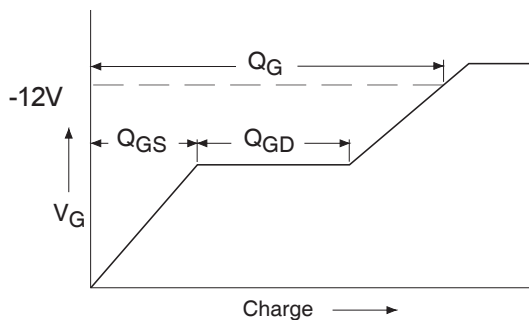


Fig 13a. Basic Gate Charge Waveform

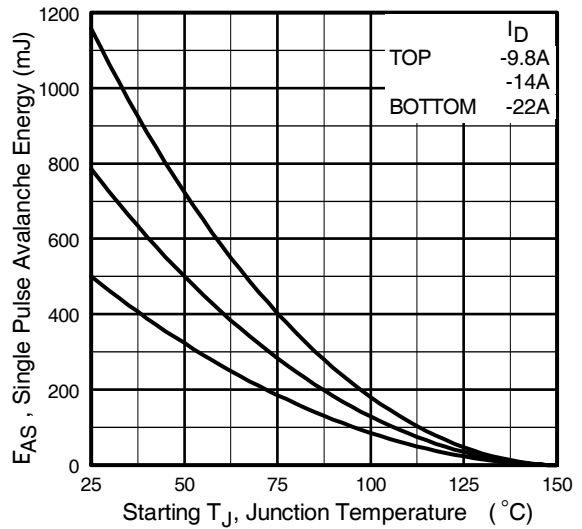


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

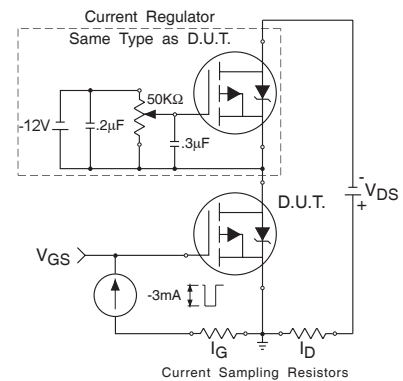
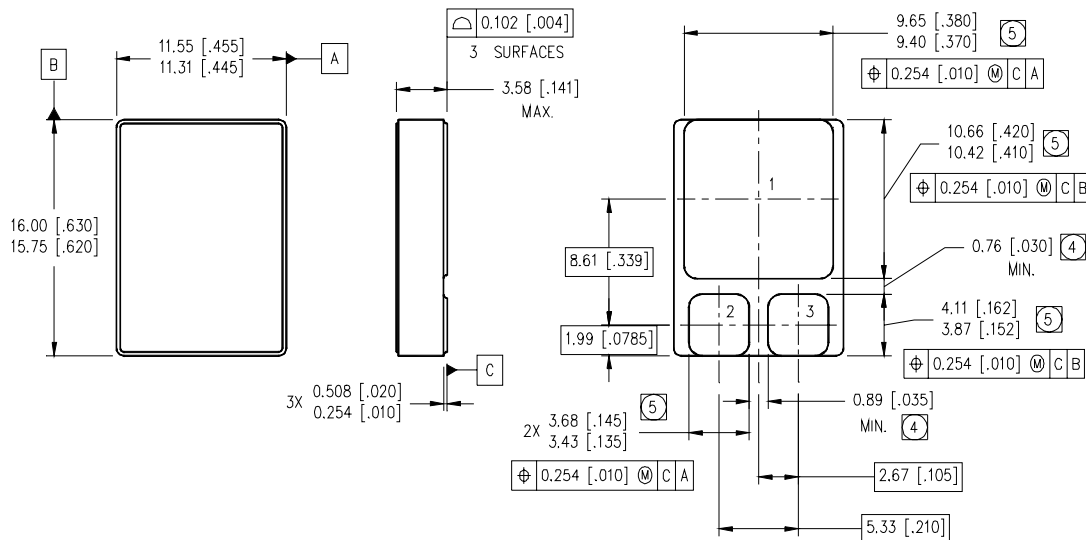


Fig 13b. Gate Charge Test Circuit

**Footnotes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = -25V$ , starting  $T_J = 25^\circ C$ ,  $L = 2.1mH$   
Peak  $I_L = -22A$ ,  $V_{GS} = -12V$
- ③  $I_{SD} \leq -22A$ ,  $di/dt \leq -450A/\mu s$ ,  
 $V_{DD} \leq -100V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
-12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
-80 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — SMD-1**



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

**PAD ASSIGNMENTS**

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE

International  
**IR** Rectifier

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